

isc Silicon PNP Power Transistor

2SB1370

DESCRIPTION

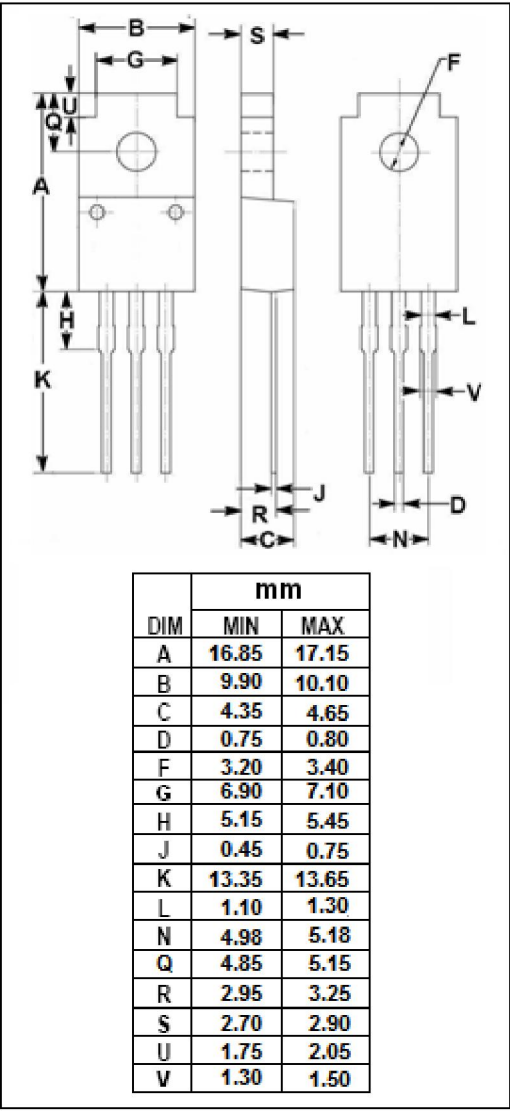
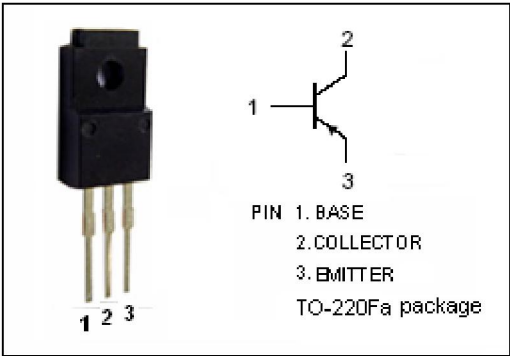
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -0.3V(Typ.)@I_C = -2A$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation

APPLICATIONS

- Designed for power switching applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-6	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	2	W
	Collector Power Dissipation @ $T_C=25^{\circ}C$	30	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB1370****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; I _B = 0	-60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -50 μ A; I _E = 0	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -50 μ A; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.5A; V _{CE} = -5V	100		320	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		80		pF
f _T	Current-Gain—Bandwidth Product	I _C =-0.5A; V _{CE} = -5V; f _{test} = 5MHz		15		MHz

◆ h_{FE} Classifications

E	F
100-200	160-320